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Electronic transport in graphene-based structures: An effective cross-section approach

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We show that transport in low-dimensional carbon structures with finite concentrations of scatterers can be modeled by utilizing scaling theory and effective cross sections. Our results are based on large-scale numerical simulations of carbon nanotubes and graphene nanoribbons, using a tight-binding model with parameters obtained from first-principles electronic structure calculations. As shown by a comprehensive statistical analysis, the scattering cross sections can be used to estimate the conductance of a quasi-one-dimensional system both in the Ohmic and localized regimes. They can be computed with good accuracy from the transmission functions of single defects, greatly reducing the computational cost and paving the way toward using first-principles methods to evaluate the conductance of mesoscopic systems, consisting of millions of atoms.

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Graphene, an effectively two-dimensional material consisting of a single sheet of carbon atoms, is regarded to be a potential candidate for a wide range of future electronic devices.1 To characterize phenomena affecting charge carrier transport in graphene-based systems, effective computational methods are required. Particularly important is the study of effects that induce a transport gap, turning graphene into a semiconductor.

The mechanisms behind experimentally measured transport gaps in graphene nanoribbons (GNRs) are currently actively studied. For a specific defect type, the scattering cross section may directly be obtained from the transmission function $T(E)$ of a conductor with one or several defects of the same type.23,24 The conductance $G(E)$ is given by the Landauer formula $G(E) = \langle 2e^2/h \rangle T(E)$. In the Ohmic regime, the expression for $\sigma(E)$ in a system with $N$ defects is

$$\sigma(E) = W \frac{T_{0}(E) - \langle T(E) \rangle}{N \langle T(E) \rangle}, \quad L \ll \xi(E),$$

where $W$ is the width of the system (or the circumference of a CNT), $T_{0}(E)$ is the transmission function of the corresponding pristine conductor, and $\langle T(E) \rangle$ is the ensemble average over different defect positions and orientations. Equation (1) is valid when the length $L$ of the conductor is much shorter than the localization length $\xi(E)$.

In the localized regime, the distribution of transmission values is not Gaussian, but rather log-normal. Thus, the typical transmission $T_{\text{typ}}(E) \equiv \exp(\ln T(E))$ is a meaningful scaling variable. In a single-mode conductor, it scales as $T_{\text{typ}}(E) \approx \exp[-L/\xi(E)]$.25 Extending the scaling law to describe a multimode conductor, such as a GNR or CNT, and treating the modes as conductors connected in parallel, we arrive at the expression

$$T_{\text{typ}}(E) = T_0(E) \exp[-L/\xi(E)].$$

In systems belonging to the orthogonal Wigner-Dyson symmetry class (e.g., graphene with short-range disorder in the absence of a magnetic field), $\xi(E)$ is related to $I_{\text{d}}(E)$ and $\sigma(E)$ through26

$$\xi(E) = \frac{T_{0}(E) + 1}2 I_{\text{d}}(E) = \frac{T_{0}(E) + 1}{2n \sigma(E)}.$$

An expression for the scattering cross section, valid in the localized regime, is obtained by combining Eqs. (2) and (3):

$$\sigma(E) = \frac{W[T_{0}(E) + 1][\ln(T_{0}(E)/T(E))]^{1/2}}{2N}, \quad L \gg \xi(E).$$
When estimating $\sigma(E)$, one has to take into account that even a single-defect system may be localized in part of the energy range. Thus the scattering cross section should be computed using both Eqs. (1) and (4), and at each energy point the smaller value should be selected as the better estimate.

We benchmark the formalism by comparing a single-defect based scattering cross section with transport results for systems with multiple defects. An unrelaxed monovacancy serves as a model defect and to exclude edge effects, we have chosen a (40,0)-CNT, with a circumference of about 10 nm, as a model system. Unrelaxed monovacancies may also be used to model adsorbate hydrogen atoms, as $sp^3$ hybridization creates a hole in the $\pi$ electron network, but also more detailed models for hydrogen adsorbates have been used.

We compute the transmission function by applying standard Green’s function based methods to a system formed by a device model, with hopping values obtained from Ref. 31. A nearest-neighbor distance of 1.42 nm is assumed, and the values are predicted to be smaller than 0.05 eV are set to zero, which in a pristine system means that hoppings to farther neighbors are excluded. The scattering cross section of a monovacancy in a (40,0)-CNT, calculated using Eq. (1), is plotted in Fig. 1, together with $T_0(E)$ and $T(E)$. As predicted by Fermi’s golden rule, the Van Hove singularities in the density of states (DOS) give rise to a greatly enhanced scattering rate near the band edges.

Next, we test how the single-defect scattering cross section compares against results for larger systems. Figures 2(a) and 2(b) show the estimated scattering cross sections given by Eqs. (1) and (4) as the length of the system is increased, keeping a constant defect density of $n = 9.6 \times 10^{-3}$ nm$^{-2}$. Each point has been obtained from an ensemble of 5000 different realizations of defect locations. The prediction of Eq. (1) grows exponentially as the length of the ribbon exceeds the expected localization length, whereas the prediction by Eq. (4) converges toward the estimate predicted by the transmission function of a single defect. Figures 2(c) and 2(d) provide more insight into the behavior of the transmission values by showing the sample skewnesses of $T$ and $\ln(T)$. The defect density is of the order of $10^{-3}$, although $T_{\text{exp}}$ is of the order of $10^{-5}$. The variance of the distribution shown in Fig. 2(f) equals 1.9 times the mean value of $-\ln(T)$, which is close to the value of two predicted by random matrix theory.

As a demonstration of the accuracy of our approach, we compare predicted and calculated localization lengths for wide ranges of energies and defect densities in Fig. 3.
The predictions are based on Eq. (3) and the single-defect scattering cross section shown in Fig. 1, whereas the calculated values have been obtained from systems ten times as long as the predicted localization lengths, using Eq. (2). Each value corresponds to an ensemble of 200 defect realizations. At low defect density, \( \xi(E) \) exhibits clear peaks, in accordance with Fig. 1, but at higher densities the peaks corresponding to the DOS of a pristine CNT are smoothed out. However, even at the highest defect density shown, the scaling approach predicts the magnitude of \( \xi(E) \) correctly. Thus we are able to predict properties of mesoscopic systems, only using the information from a single-defect calculation.

Based on Kubo-Greenwood (KG) simulations, it has been proposed that topological defects, such as Stone-Wales defects and 555777 defects, exhibit fingerprint-like scattering properties \(^{34}\) A Stone-Wales defect is a metastable bond rotation, consisting of two pentagons and two heptagons embedded in the graphene lattice, whereas a 555777 defect is a relaxed form of a divacancy, consisting of three pentagons and three heptagons. \(^{35}\) Such defects are expected to be found in irradiated graphene, where especially 555777 defects may occur in relatively high concentrations. \(^{36}\) Figure 4(a) compares transport results for a 16-atom-wide armchair-edged GNR (AGNR), containing a single Stone-Wales defect, obtained both from a modified TB model and the density functional theory (DFT). The TB hopping parameters are obtained from the relaxed bond lengths around the defects, acquired from the SIESTA implementation \(^{37,38}\) of DFT and the DFT transport results are from the TRANSIESTA code. \(^{39,40}\)

In Fig. 4(b), we show bulk scattering cross sections for three defects, computed by applying \( k \)-space sampled periodic boundary conditions in the transverse direction. \(^{41}\) Although retaining the same general shape as the one shown in Fig. 1, the scattering cross section of a monovacancy is now considerably smoother. At low defect densities of up to roughly \( 10^{-3} \) defects per atomic site, the scattering cross section for monovacancies fits both qualitatively and quantitatively the corresponding KG based mean free paths. \(^{32}\) Also the scattering cross sections for Stone-Wales and 555777 defects agree fairly well with recent KG results, \(^{34}\) although those are based on a somewhat differently parametrized TB model. When comparing against KG results, one has to remember that due to the phenomenon of minimum conductivity, \(^{17,43}\) two-dimensional graphene will not enter the localized regime. At very high densities, the defects lose their pointlike nature, and the scattering cross-section formalism breaks down. Additionally, a high density of defects will contribute to the transmission through an impurity band. \(^{38}\)

We next test the predictive power of the scattering cross-section approach. If a system contains several different types of defects, one can estimate the average and typical transmissions from

\[
\langle T(E) \rangle = \frac{T_0(E)}{1 + L \sum_i n_i \sigma_i(E)} \quad L \ll \xi(E),
\]

and

\[
T_{\text{typ}}(E) = \frac{T_0(E)}{\exp \left[ \frac{L}{\xi(E)} \sum_i n_i \sigma_i(E) \right]} \quad L \gg \xi(E).
\]

We define the localized domain as the region where \( T_{\text{typ}}(E) \), given by Eq. (6), is smaller than \( \langle T(E) \rangle \), given by Eq. (5).

Figure 5 shows calculated mean and typical transmission functions for a 1.3 \( \mu \)m long and 30 nm wide AGNR with 100 each of monovacancies, Stone-Wales defects, and 555777 defects.
departs, together with corresponding predictions obtained using Eqs. (5) and (6). The transmissions have been calculated using the TB model, based on an ensemble of 12 defect realizations, whereas the predictions are based on the bulk scattering cross sections shown in Fig. 4(b). As the results indicate, the mean or typical transmission in a realistically wide GNR or CNT can be estimated by only calculating the transmission functions for single defects in an edgeless system. The estimates are slightly lower than the actual mean and transmission functions for single defects in an edgeless system. It indicates the mean or typical transmission in a realistically wide GNR or CNT can be estimated by only calculating the transmission functions for single defects.

In summary, we have presented numerical simulations showing that effective scattering cross sections for defects, combined with scaling theory, can be used to estimate the transport properties of graphene-based devices of sizes ranging from nano- to micrometers. In particular, their conductances can be predicted both in the Ohmic and strongly localized regimes. As the scattering cross section can be computed from small-scale systems, possibilities to model systems beyond the reach of present-day methods are opened.

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1. A. Geim and K. Novoselov, Nat. Mater. 6, 183 (2007).
17. N. M. R. Peres, Rev. Mod. Phys. 82, 2673 (2010).
33. The sample skewness is defined as the ratio $m_3/m_2^{3/2}$, where $m_3$ is the sample third central moment and $m_2$ the sample variance.
39. We use a double-ζ polarization basis set together with a 250 Ry mesh cutoff and the PBE-GGA functional for electron exchange and correlation. Ionic coordinates are relaxed using a conjugate gradient.

We thank Troels Markussen for useful comments.
algorithm until the force on each atom is within 0.02 eV/Å. Electron transmission is calculated with a single-ζ polarization basis set.


41 We compute the bulk scattering cross sections from a system with a single defect in a 20 nm wide computational unit cell, by averaging over the different defect orientations in the armchair direction and by using 20 $k$-space points.
